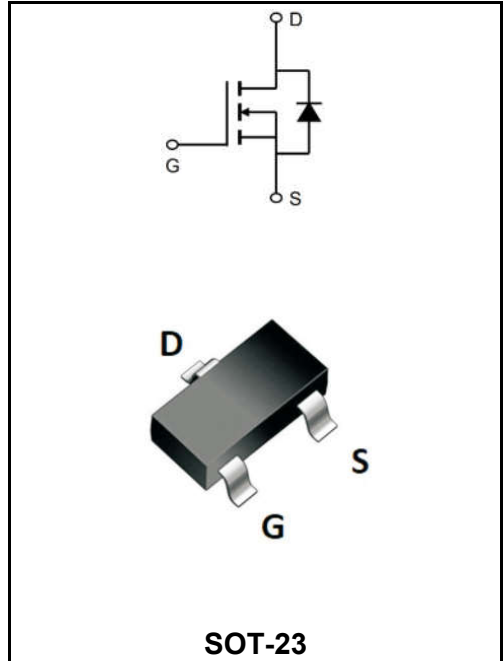


30V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	4.2A
V_{DSS}	30V
R_{DS(on)-typ(@V_{GS}=10V)}	< 42mΩ (Type:32 mΩ)



Application

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply

Product Specification Classification

Part Number	Package	Marking	Pack
YFW3400CI	SOT-23	A09T..	3000PCS/Tape

Maximum Ratings at T_c=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate - Source Voltage	V_{GS}	± 12	V
Continuous Drain Current T _A =25°C	I_D	4.2	A
Continuous Drain Current T _A =100°C	I_D	2.6	A
Pulsed Drain Current	I_{DM}	16	A
Power Dissipation T _A = 25°C	P_D	1.1	W
Thermal Resistance, Junction to Case	R_{θJA}	113.6	°C/W
Operating Junction Temperature Range	T_J , T_{STG}	-55 to +150	°C

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	V(BR)DSS	30	32	-	V
Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$	I_{DSS}	-	-	1.0	μA
Gate to Body Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	V_{GS(th)}	0.5	0.9	1.4	V
Static Drain-Source on-Resistance note2	$V_{GS}=10V, I_D=4A$	R_{DS(ON)}	-	32	42	mΩ
	$V_{GS}=4.5V, I_D=3A$		-	36	48	
	$V_{GS}=2.5V, I_D=2A$		-	50	70	
Input Capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	285	-	pF
Output Capacitance		C_{oss}	-	33	-	
Reverse Transfer Capacitance		C_{rss}	-	27	-	
Total Gate Charge	$V_{DS}=15V$ $V_{GS}=4.5V$ $I_D=4A$	Q_g	-	2.6	-	nC
Gate-Source Charge		Q_{gs}	-	0.6	-	
Gate-Drain("Miller") Charge		Q_{gd}	-	0.9	-	
Turn-on delay time	$V_{DS}=15V, I_D=2A,$ $R_{GEN}=3\Omega, V_{GS}=4.5V$	t_{d(on)}	-	15	-	ns
Turn-on Rise Time		T_r	-	42	-	
Turn-Off Delay Time		t_{d(OFF)}	-	16	-	
Turn-Off Fall Time		t_f	-	10	-	
Maximum Continuous Drain to Source Diode Forward Current		I_S	-	-	4	A
Maximum Pulsed Drain to Source Diode Forward Current		I_{SM}	-	-	16	A
Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=4A$	V_{SD}	-	-	1.2	V

Note :

- 1、 The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width $\cong 300\mu s$, duty cycle $\cong 2\%$
- 3、 The power dissipation is limited by 150°C junction temperature
- 4、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

Typical Characteristics

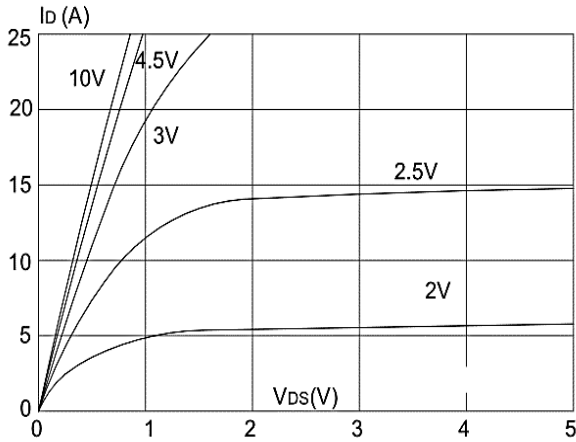


Figure 1: Output Characteristics

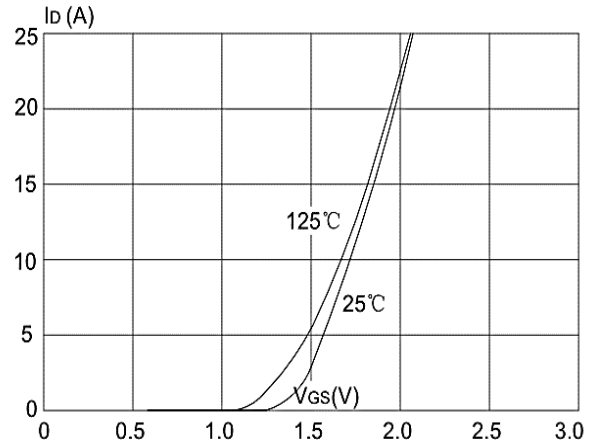


Figure 2: Typical Transfer Characteristics

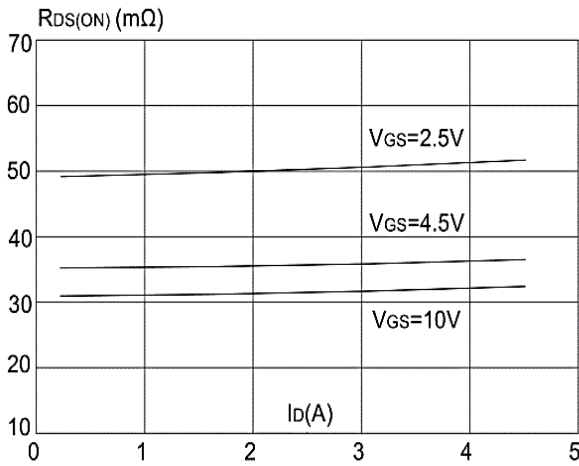


Figure 3: On-resistance vs. Drain Current

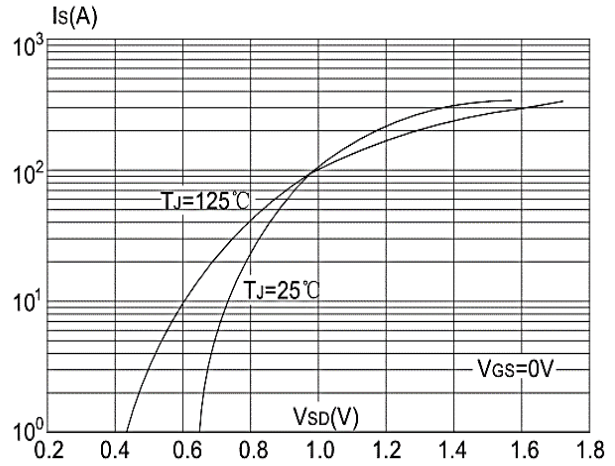


Figure 4: Body Diode Characteristics

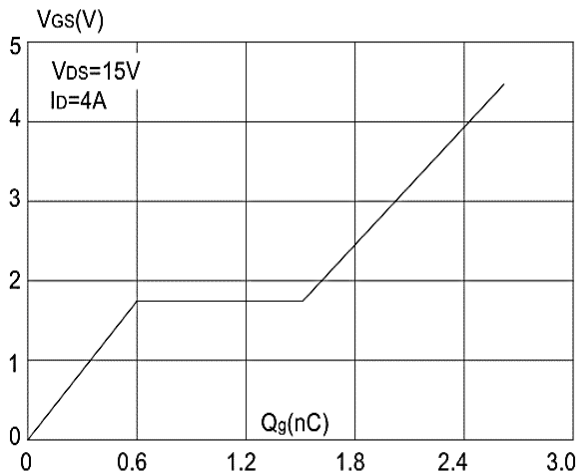


Figure 5: Gate Charge Characteristics

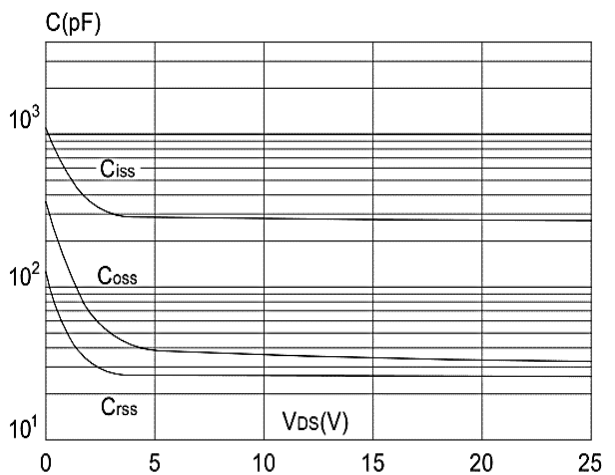


Figure 6: Capacitance Characteristics

Ratings and Characteristic Curves

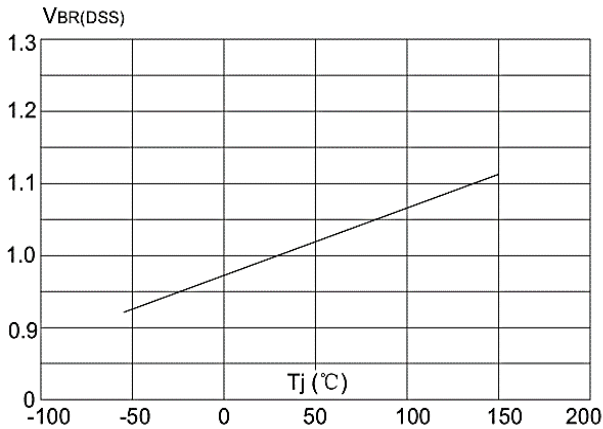


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

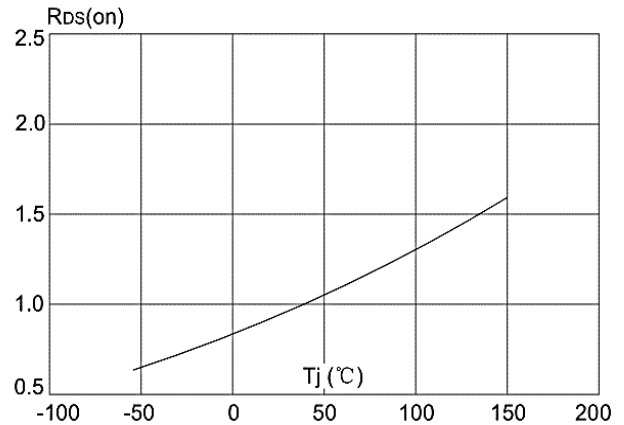


Figure 8: Normalized on Resistance vs. Junction Temperature

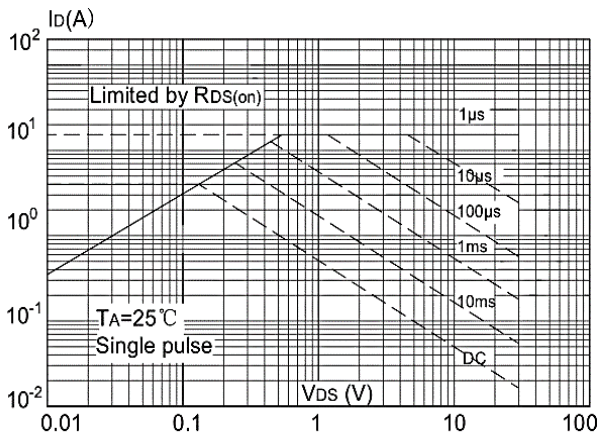


Figure 9: Maximum Safe Operating Area

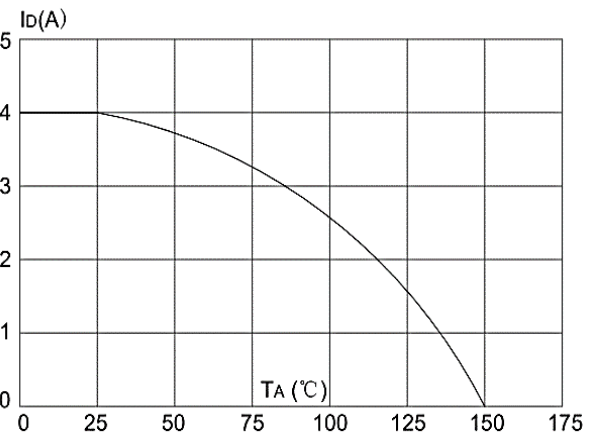


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

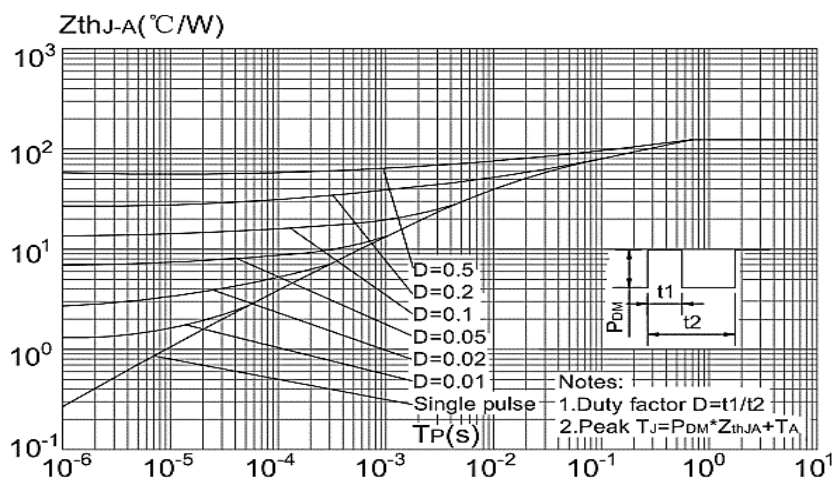
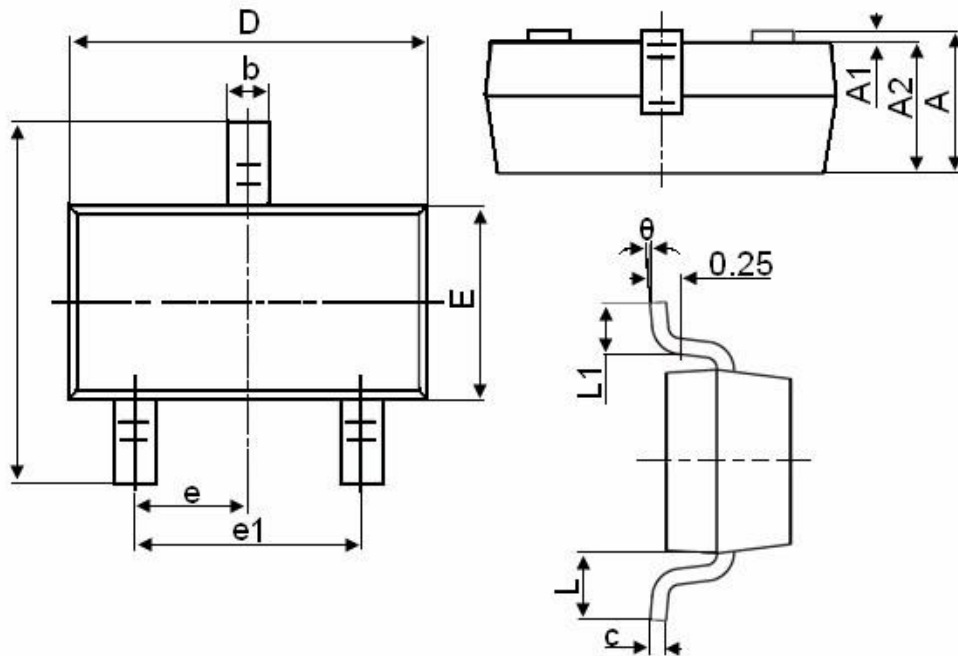


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien

SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°